

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP330

PROGRAMMABLE CONTROLLERS

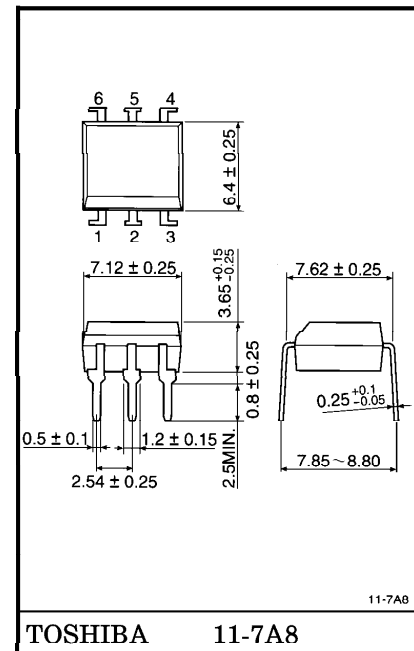
AC/DC-INPUT MODULE

TELECOMMUNICATION

The TOSHIBA TLP330 consists of a photo-transistor optically coupled to two gallium arsenide infrared emitting diode connected inverse parallel in a six lead plastic DIP package. This is suitable for application of AC input current up to 150mA.

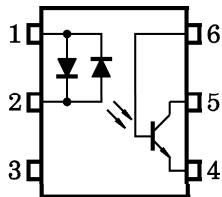
- I_F Maximum Rating : $\pm 150\text{mA}$
- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 25% (Min.) ($I_F = \pm 20\text{mA}$)
- Isolation Voltage : 5000Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



Weight : 0.39g

PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE, CATHODE
- 2 : CATHODE, ANODE
- 3 : NC
- 4 : EMITTER
- 5 : COLLECTOR
- 6 : BASE

961001EBC2

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to foreign exchange and foreign trade control laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I_F	± 150	mA
	Forward Current Derating ($T_a \geq 25^\circ\text{C}$)	$\Delta I_F / ^\circ\text{C}$	-1.5	mA / $^\circ\text{C}$
	Peak Forward Current (100 μs pulse, 100pps)	I_{FP}	± 1	A
	Junction Temperature	T_j	125	$^\circ\text{C}$
DETECTOR	Collector-Emitter Voltage	V_{CEO}	55	V
	Collector-Base Voltage	V_{CBO}	80	V
	Emitter-Collector Voltage	V_{ECO}	7	V
	Emitter-Base Voltage	V_{EBO}	7	V
	Collector Current	I_C	80	mA
	Power Dissipation	P_C	150	mW
	Power Dissipation Derating ($T_a \geq 25^\circ\text{C}$)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / $^\circ\text{C}$
	Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \sim 125$	$^\circ\text{C}$
Operating Temperature Range		T_{opr}	$-55 \sim 100$	$^\circ\text{C}$
Lead Soldering Temperature (10s)		T_{sol}	260	$^\circ\text{C}$
Total Package Power Dissipation		P_T	250	mW
Total Package Power Dissipation Derating ($T_a \geq 25^\circ\text{C}$)		$\Delta P_T / ^\circ\text{C}$	-2.5	mW / $^\circ\text{C}$
Isolation Voltage (AC, 1 min, R.H. $\leq 60\%$) (Note 1)		BV_S	5000	V _{rms}

(Note 1) Device considered a two terminal device : Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}	—	5	24	V
Forward Current	I_F (RMS)	—	20	120	mA
Collector Current	I_C	—	1	10	mA
Operating Temperature	T_{opr}	-25	—	85	$^\circ\text{C}$

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = \pm 100\text{mA}$	—	1.4	1.7	V
	Forward Current	I_F	$V_F = \pm 0.7\text{V}$	—	2.5	20	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	100	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Collector Dark Current	I_{CER}	$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1\text{M}\Omega$	—	0.5	10	μA
	Collector Dark Current	I_{CBO}	$V_{CB} = 10\text{V}$	—	0.1	—	nA
	DC Forward Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 0.5\text{mA}$	—	400	—	—
	Capacitance (Collector to Emitter)	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = \pm 20\text{mA}, V_{CE} = 1\text{V}$	25	—	—	%
	$I_C / I_F (\text{high})$	$I_F = \pm 100\text{mA}, V_{CE} = 1\text{V}$	20	—	80	%
Base Photo-Current	I_{PB}	$V_F = \pm 5\text{mA}, V_{CB} = 5\text{V}$	—	10	—	μA
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 2.4\text{mA}, I_F = 20\text{mA}$	—	—	0.4	V
		$I_C = 2.4\text{mA}, I_F = \pm 100\text{mA}$	—	—	0.4	
Off-State Collector Current	$I_C (\text{off})$	$V_F = \pm 0.7\text{V}, V_{CE} = 24\text{V}$	—	1	10	μA
CTR Symmetry	$I_C (\text{ratio})$	$I_C (I_F = -20\text{mA})$ $/ I_C (I_F = +20\text{mA})$	0.5	1	2	—

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	CS	VS=0, f=1MHz	—	0.8	—	pF
Isolation Resistance	RS	VS=500V, R.H.≤60%	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation Voltage	BVS	AC, 1 minute	5000	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	Vrms
		DC, 1 minute, in oil	—	10000	—	Vdc

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr	VCC=10V IC=2mA RL=100Ω	—	2	—	μs
Fall Time	tf		—	3	—	
Turn-on Time	ton		—	3	—	
Turn-off Time	toff		—	3	—	
Turn-on Time	tON	RL=1.9kΩ (Fig.1) RBE=OPEN VCC=5V, IF=±16mA	—	2	—	μs
Storage Time	ts		—	15	—	
Turn-off Time	tOFF		—	25	—	
Turn-on Time	tON	RL=1.9kΩ (Fig.1) RBE=220kΩ VCC=5V, IF=±16mA	—	2	—	μs
Storage Time	ts		—	12	—	
Turn-off Time	tOFF		—	20	—	

Fig.1 Switching Time Test Circuit

